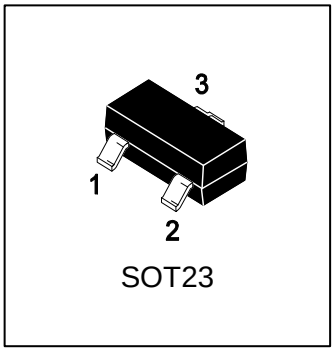
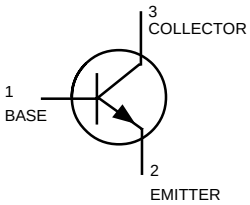
L2SC2412KRLT1G
S-L2SC2412KRLT1G

General Purpose Transistors NPN Silicon



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L2SC2412KRLT1G	BR	3000/Tape&Reel
L2SC2412KRLT3G	BR	10000/Tape&Reel

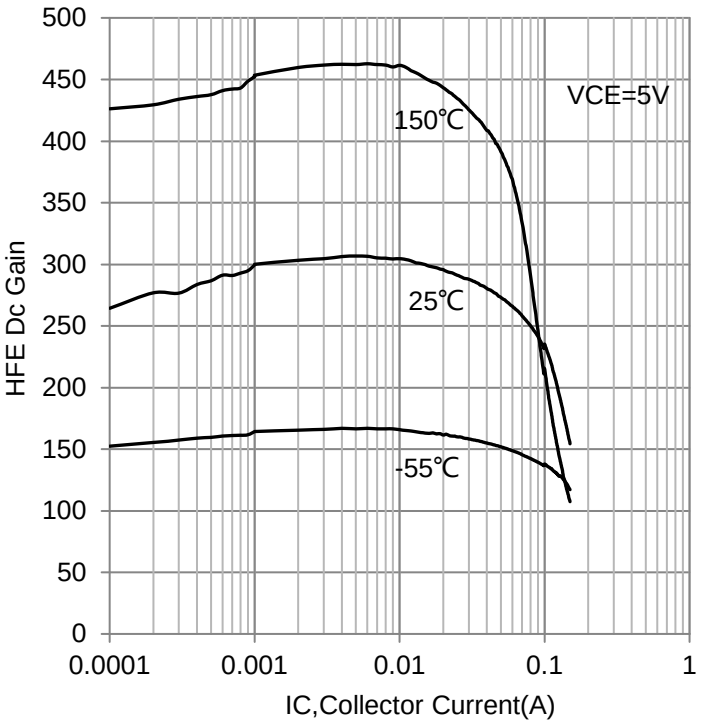
3. MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Collector-Emitter Voltage	VCEO	50	V
Collector-Base voltage	VCBO	60	V
Emitter-Base Voltage	VEBO	7	V
Collector current —Continuous	IC	150	mA
Collector power dissipation	PC	225	mW
Junction temperature	Tj	150	℃
Storage temperature	Tstg	-55~+150	℃

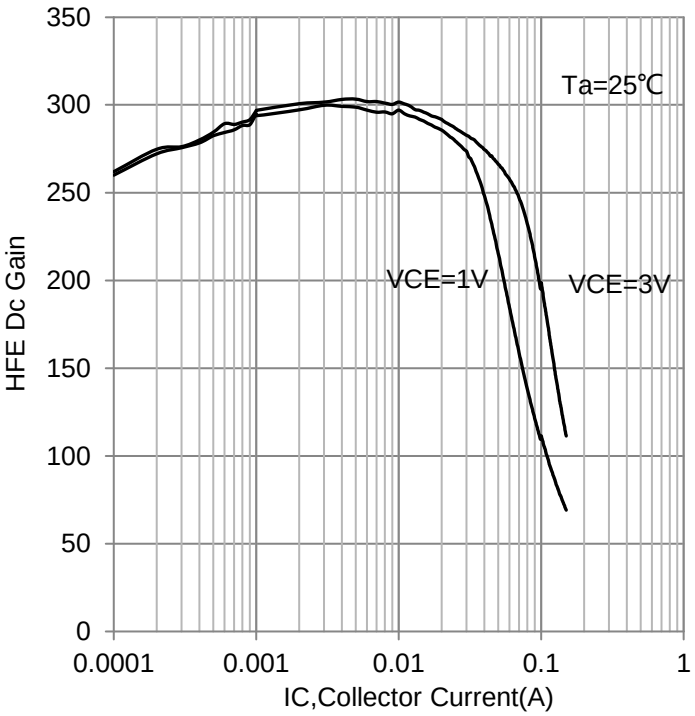
4. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage (IC =1.0mA)	V(BR)CEO	50	-	-	V
Emitter-Base Breakdown Voltage (IE = 50μA)	V(BR)EBO	7	-	-	V
Collector-Base Breakdown voltage (IC = 50μA)	V(BR)CBO	60	-	-	V
Collector Cutoff Current (VCB = 60 V)	ICBO	-	-	0.1	μA
Emitter Cutoff Current (VEB = 7V)	IEBO	-	-	0.1	μA
Collector-Emitter Saturation Voltage (IC / IB = 50 mA / 5m A)	VCE(S)	-	-	0.4	V
Base–Emitter Saturation Voltage (IC = 100mA, IB = 10mA)	VBE(S)	-	-	1.1	V
DC current transfer ratio (VCE = 6 V, IC = 1mA)	hFE	180	-	390	
Transition frequency (VCE = 12 V, IE = 2mA, f =30MHz)	fT	-	180	-	MHz
Output capacitance (VCB = 12 V, IE = 0A, f =1MHz)	Cob	-	2	3.5	pF

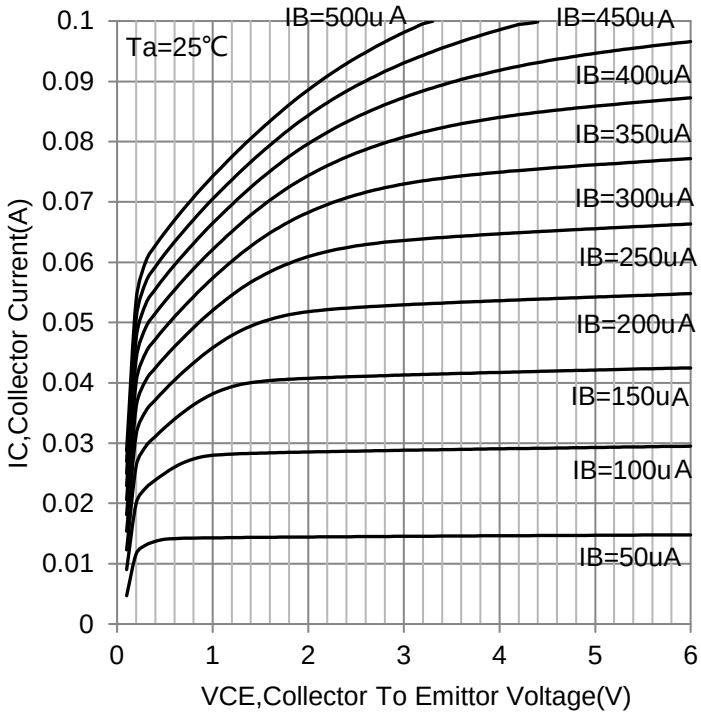
5.ELECTRICAL CHARACTERISTICS CURVES



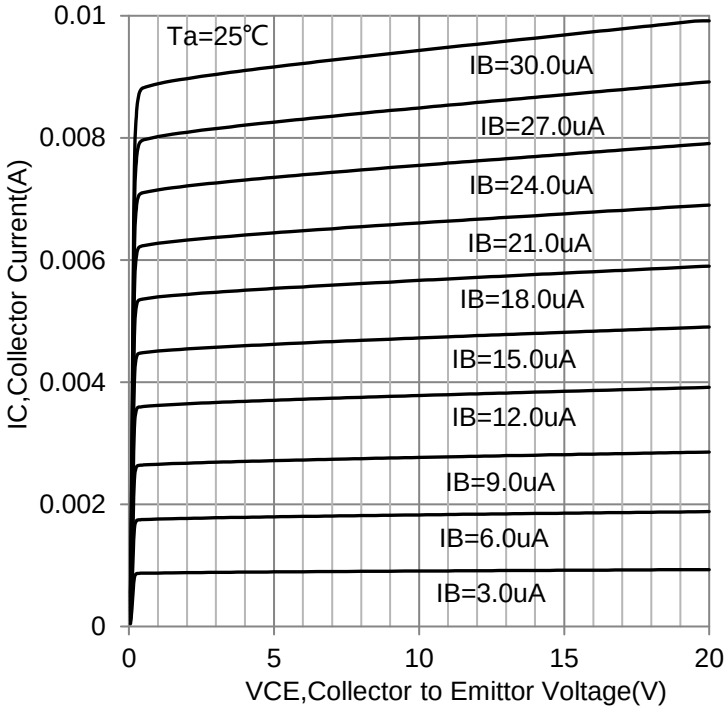
HFE vs. IC



HFE vs. IC

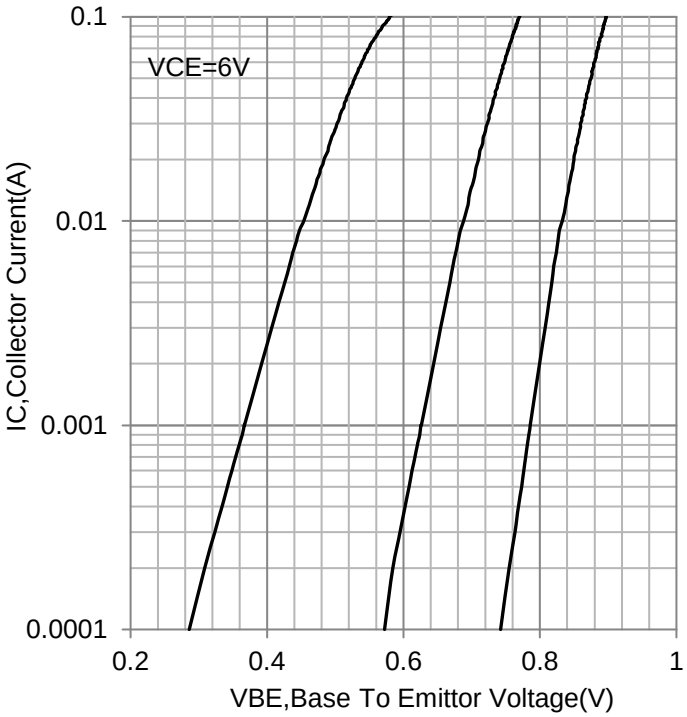


IC vs. VCE

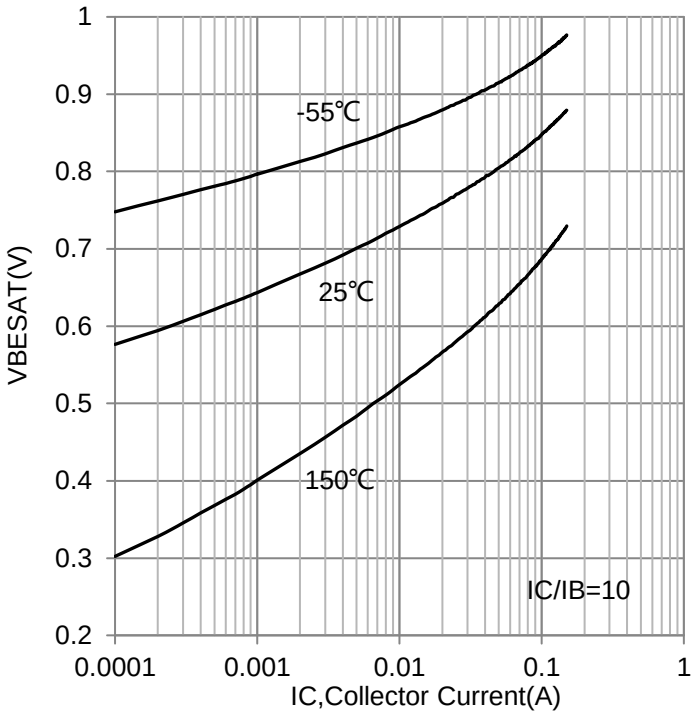


IC vs. VCE

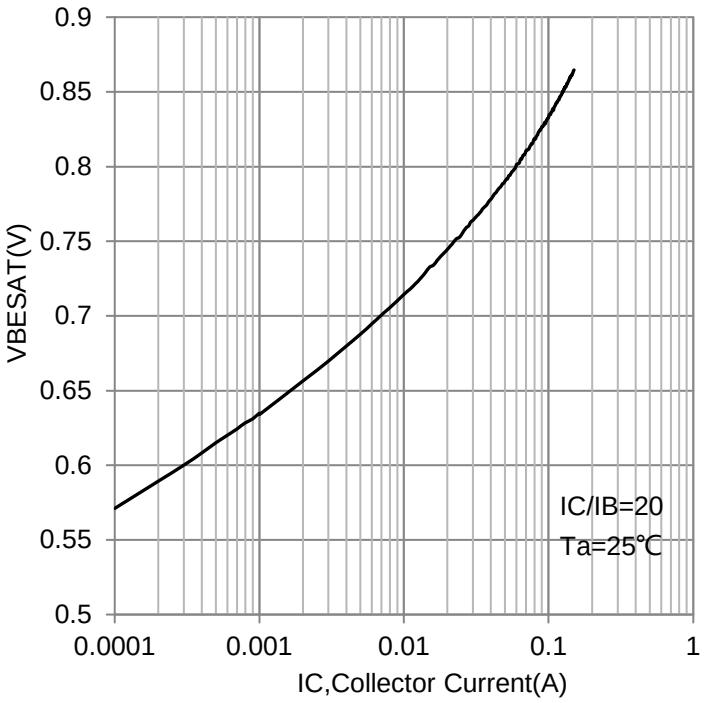
5.ELECTRICAL CHARACTERISTICS CURVES(Con.)



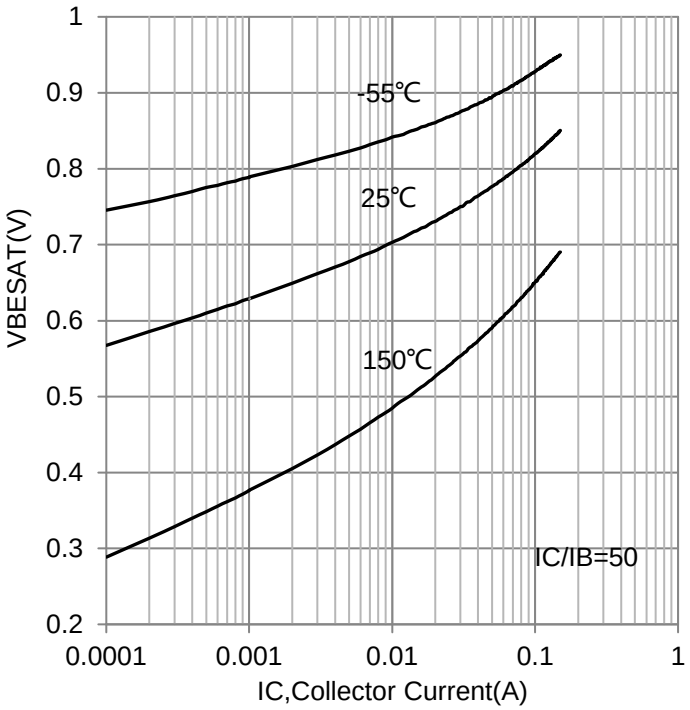
VBE vs. IC



VBESAT vs. IC

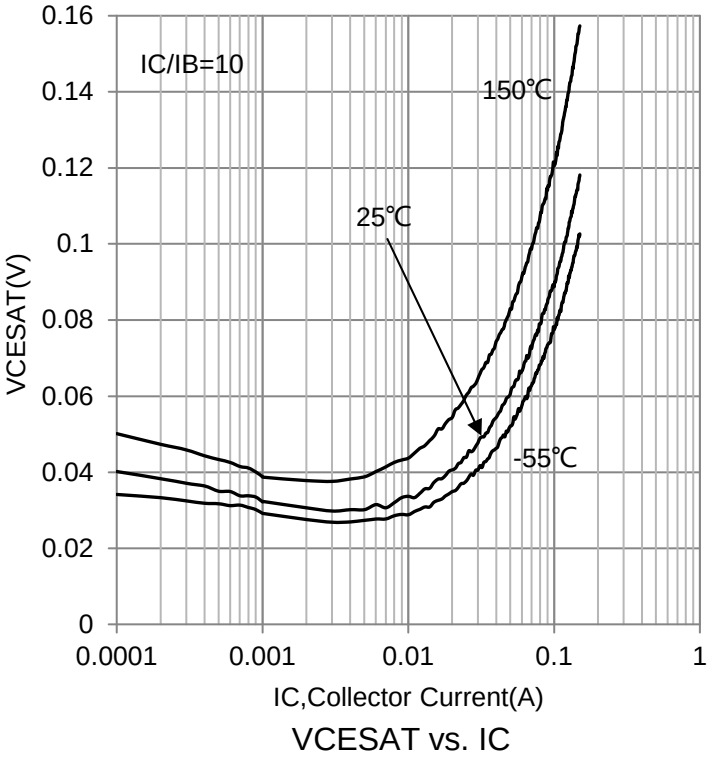


VBESAT vs. IC

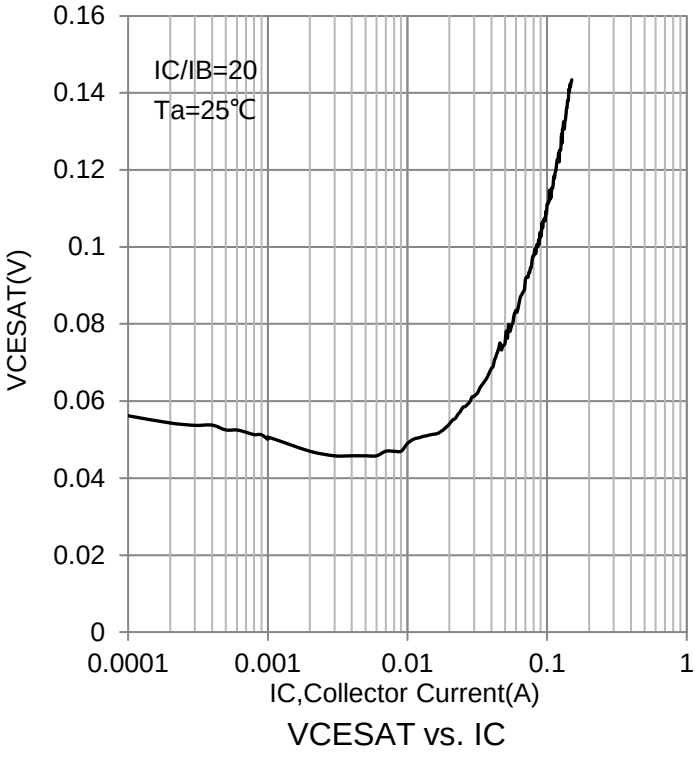


VBESAT vs. IC

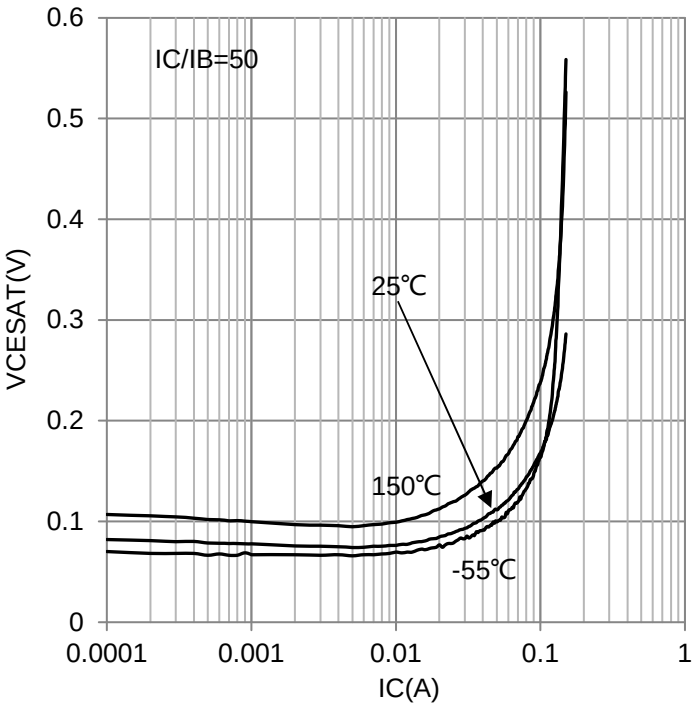
5.ELECTRICAL CHARACTERISTICS CURVES(Con.)



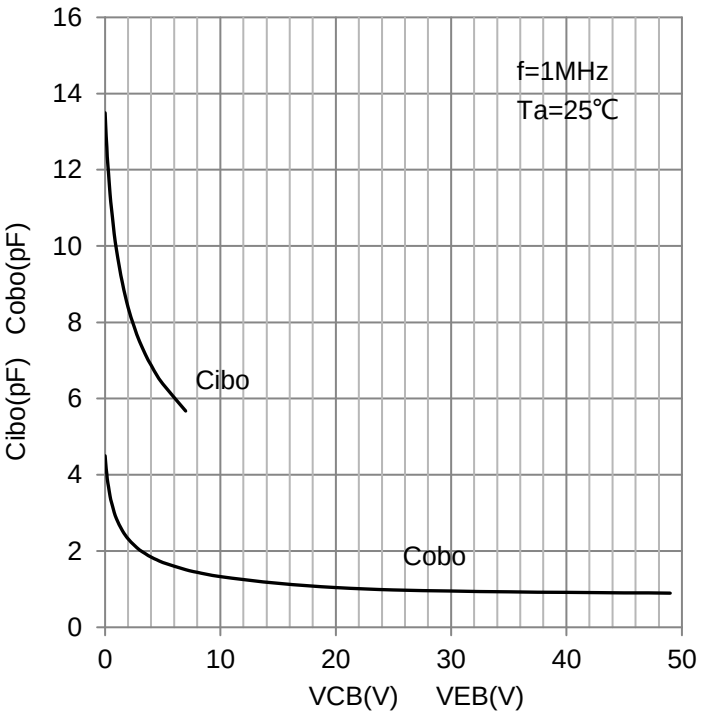
VCESAT vs. IC



VCESAT vs. IC

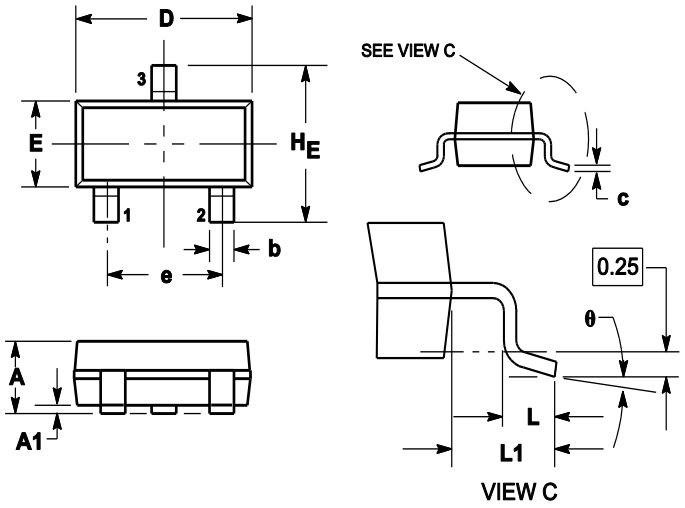


VCESAT vs. IC



Capacitance

6.OUTLINE AND DIMENSIONS

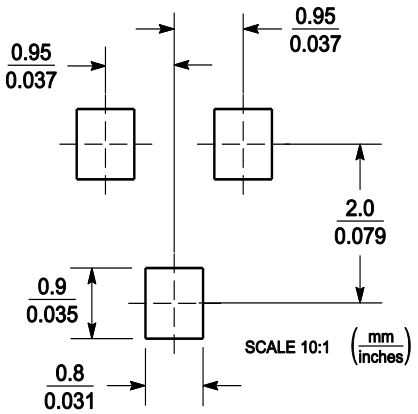


Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

7.SOLDERING FOOTPRINT



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.

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